

## **INCHANGE SEMICONDUCTOR**

# isc N-Channel MOSFET Transistor

## IRF3256,IIRF3256

#### FEATURES

- Static drain-source on-resistance:
  - R⊳s(on) ≤3.4mΩ
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits

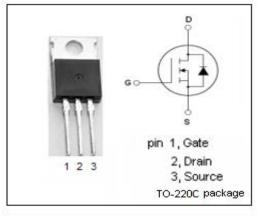
## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

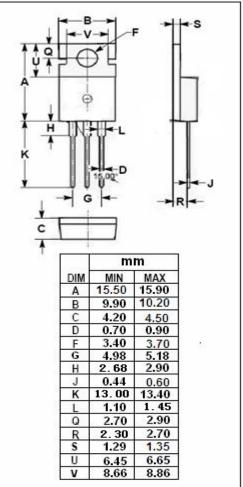
SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>DSS</sub>	Drain-Source Voltage	60	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
ID	Drain Current-Continuous	A		
I <sub>DM</sub>	Drain Current-Single Pulsed	820	А	
PD	Total Dissipation @T <sub>C</sub> =25°C	300	W	
Tj	Max. Operating Junction Temperature	175	°C	
T <sub>stg</sub>	Storage Temperature	-55~175	°C	

#### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.5	°C <b>/W</b>
Rth(ch-a)	Channel-to-ambient thermal resistance	62	℃ <b>/W</b>

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### ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; ID = 1mA	60			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =150 μ A	2		4	v
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =75A			3.4	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V			<b>±</b> 100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =60V; V <sub>GS</sub> = 0V			20	μA
V <sub>SD</sub>	Diode forward voltage	Is =75A; V <sub>GS</sub> = 0 V			1.3	V

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